

μ PD72065/65B CMOS Floppy-Disk Controller

Description

The μ PD72065/65B CMOS Floppy-Disk Controller (FDC) is NEC's follow-on to the μ PD765A/B. (μ PD72065B is a functionally enhanced version of μ PD72065.) The FDC is an LSI chip containing the circuitry and control functions for interfacing a processor to four floppy-disk drives (FDDs). It is capable of either IBM 3740 single-density format (FM) or IBM system 34 double-density format (MFM), including double-sided recording.

Control signals of the FDC simplify the design of an external phase-locked loop and write precompensation circuitry. The FDC simplifies and handles most of the burdens associated with implementing a floppy-disk interface.

Handshaking signals of the FDC make DMA operation easy to incorporate with the aid of an external DMA controller chip, such as the μ PD8257. In DMA mode, the processor need only load the command into the FDC; all data transfers occur under control of the FDC and DMA controllers. In non-DMA mode, the FDC generates interrupts to the processor every time a data byte is to be transferred.

The FDC will execute the 19 commands listed below. Most of the commands require multiple 8-bit bytes to fully specify the operation that the processor wants the FDC to perform.

Read Data
Read ID
Specify
Read Diagnostics
Scan Equal
Scan High or Equal
Scan Low or Equal
Sense Drive Status
Reset Standby
Version

Read Deleted Data Write Data Write ID

Write Deleted Data Seek Recalibrate

Sense Interrupt Status Set Standby Software Reset

Features

Internal address mark detection circuitry of the FDC simplifies the phase-locked loop and read electronics. Track stepping, head load time, and head unload time are user-programmable. Additional features are multi-track and multiside read and write commands plus single- and double-density capabilities.

- 100% 765A/B microcode compatibility
- Sony (ECMA) compatible recording format
- IBM-compatible format (single- and double-density)
- Multisector and multitrack transfer capability
- Interface processor with up to four floppy-disk or microfloppy-disk drives
- Data scan capability: single sector or entire cylinder, comparing host memory and disk data byte-by-byte
- Data transfers in DMA and non-DMA modes
- Parallel seek operations on up to four disk drives
- Compatible with μPD8080/85, μPD8086/88, and μPD780 (Z80[®]) microprocessors
- □ Single-phase clock (8 MHz maximum)
- □ +5-volt power supply
- CMOS technology

Ordering Information

Part Number	Package						
μPD72065C	40-pin plastic DIP (600 mil)						
65G	52-pin plastic miniflat (3.5-mm leads)						
65GC	52-pin plastic miniflat (1.8-mm leads)	3					
65L	44-pin PLCC						
μPD72065BC	40-pin plastic DIP (600 mil)						
65BGC-3B6	52-pin plastic miniflat (1.8-mm leads)	2, 3					
65BL	44-pin PLCC	2					

Notes:

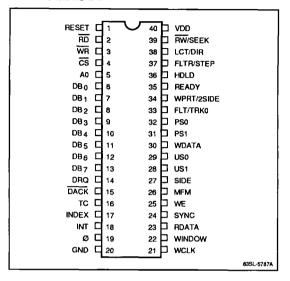
- The basic part numbers are μPD72065 and μPD72065B. Suffix codes are added to identify particular packages.
- (2) The part is under development.
- (3) Surface-mount conditions differ among the miniflat packages, as in reflow soldering. The NEC sales staff can provide details.

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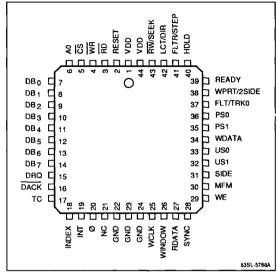


Pin Configurations

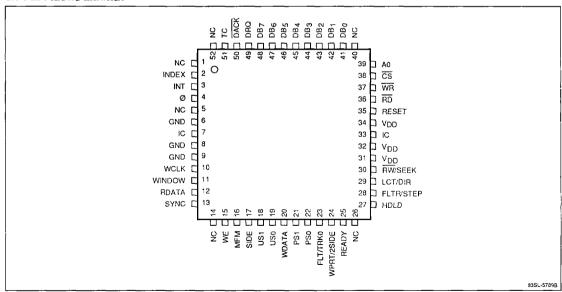
40-Pin Plastic DIP



44-Pin PLCC (Plastic Leaded Chip Carrier)



52-Pin Plastic Miniflat





Pin Identification

Symbol	I/O	Function							
A0	ln	Via the address bus, selects internal status register (0) or data register (1)							
CS	In	Chip select. Enables RD and WR signals.							
DACK	ln	DMA acknowledge.							
DB ₀ -DB ₇	1/0	Bidirectional three-state data bus. At reset, bus goes to input mode.							
DRQ	Out	DMA request. Request for data transfer in DMA mode.							
FLT/TRKO	In	FLT (Fault). In read/write operation (RW/SEEK pin = 0), indicates whether FDD is in fault state.							
		TRK0 (Track 0). In seek operation (RW/SEEK pin = 1), indicates whether FDD read/write head is positioned at cylinder 0.							
FLTR/STEP	Out	FLTA (Fault read). In read/write operation (RW/SEEK pin = 0), releases FDD fault state.							
		STEP. In seek operation (RW/SEEK pin = 1), outputs seek pulses.							
HDLD	Out	Head load. Sets FDD read/write head to load state.							
INDEX	ìn	Indicates that FDD read/write head is on the physical starting point of the track.							
INT	Out	Interrupt request. Requests main system to deal with transfer of data or result of execution.							
LCT/DIR	Out	LCT (Low current). In read/write operation (RW/SEEK pln = 0), indicates FDD read/write head is selecting a cylinder beyond the 42nd.							
		DIR. In seek operation (RW/SEEK pin = 1), specifies direction, toward the outside (0) or the inside (1).							
MFM	Out	Specifies function mode of VFO circuits: 0 = FM; 1 = MFM.							
PS0, PS1	Out	Preshift signal requesting WDATA bit to shift in the opposite direction of expected peak shift to cancel out peak shift created when writing in MFM mode.							
		PS0 PS1 FM MFM 0 0 No No shift 0 1 shift Delays WDATA bit 1 0 Advances WDATA bit							
RD	in	Control signal used by main system to read out data from FDC to data bus.							

Symbol	I/O	Function
RDATA	ln	Data (clock and data bits) read out from FDD.
		Unless both WINDOW and RDATA are input at read operation, FDC will enter deadlock state.
READY	ln	indicates FDD is in ready state.
RESET	ln	Sets FDC to idle state as follows.
		Drive interface outputs except PS0, PS1, and WDATA (undefined) are set to low.
		In the main system, INT and DRQ are set to low and ${\rm DB_0\text{-}DB_7}$ are set to input mode.
RW/SEEK	Out	Selects read/write operation (0) or seek operation (1).
SIDE	Out	Selects head 0 (SIDE = 0) or head 1 (SIDE = 1) in a double-sided FDD.
SYNC	Out	VFO synchronize. Indicates FDC functional mode: read operation (1) or read operation inhibited (0).
TC	ln	Terminal count. Request for data transfer termination.
US0, US1	Out	Unit select. One of four FDDs is selected by decoding US0 and US1.
WCLK	in	Write clock. Timing signal for data transfer in write operation; should also be input in read operation.
		Rising edges of WCLK and ϕ must be synchronized for μ PD72065 but not for μ PD72065B.
		WCLK = 16 ϕ cycles in FM mode and 8 ϕ cycles in MFM mode.
ATADW	Out	Write data (clock and data bits) to FDD.
WE	Out	Write enable. Requests write operation to FDD.
WINDOW	In	Data window signal generated by VFO circuit and used for sampling the clock and data bits of RDATA. Discrimination between clock and data bits is done in the FDC.
WPRT/2SIDE	ln	WPRT (Write protected). In read/write operation (RW/SEEK pin = 0), indicates whether media is in write inhibit state.
		2SIDE. In seek operation (FW/SEEK pin = 1), indicates whether a double-sided floppy disk is inserted.

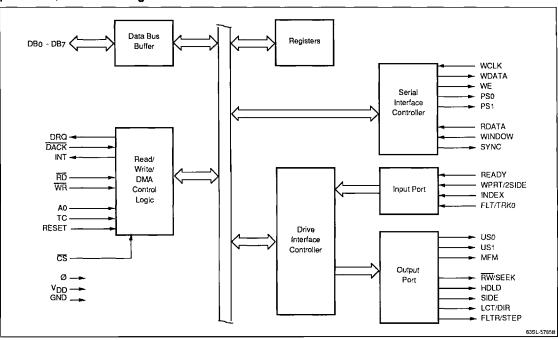


Pin Identification (cont)

Symbol	I/O	Function
WR	ln	Control signal used by main system to write data on data bus to FDC.
φ	ln	Single-phase clock: standard floppy, 8 MHz; minifloppy, 4 MHz.
GND		Ground
V _{DD}	ln	+5-volt power supply
IC		Internal connection; must be left open.
NC		No connection.

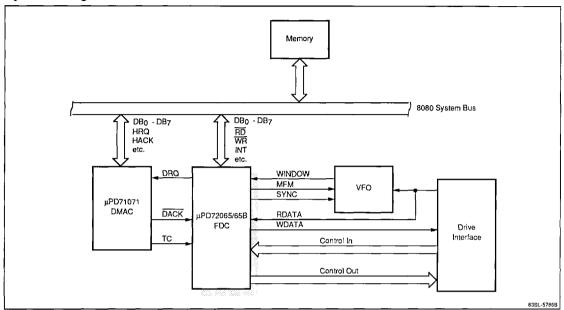
Note: At reset, all output pins go to the low state except for pins PS0 and PS1, whose state is undefined.

μPD72065/65B Block Diagram





System Configuration



Absolute Maximum Ratings $T_A = +25^{\circ}C$

Voltage on any pin	-0.5 to +7 V
Operating temperature, T _{OPT}	-10 to +70°C
Storage temperature, T _{STG}	65 to +150°C

Capacitance

 $T_A = +25^{\circ}C; V_{DD} = 0 V; f = 1 MHz$

Parameter	Symbol	Min	Max	Unit	Conditions
Clock capacitance	Сф		20	рF	Unmeasured pins returned to 0 V.
Input capacitance	C _{IN}		10	pF	•
Output capacitance	C _{OUT}		20	pF	•

μPD72065/65B



DC Characteristics

 $T_A = -10 \text{ to } +70^{\circ}\text{C}; V_{DD} = +5 \text{ V} \pm 10\%$

Parameter	Symbol	Min	Max	Unit	Conditions
Input voltage, low	V∤ _{IL}	- 0.5	8.0	٧	
Input voltage, high	VIIH	2.2	V _{DD} + 0.5	V	
Input voltage, low (φ, WCLK)	V _{IL}	- 0.5	0.65	٧	
input voltage, high (φ, WCLK)	V _{IH}	2.2	V _{DD} + 0.5	V	
Output voltage, low	V _{OL}		0.45	٧	I _{OL} ≈ 2.0 mA
Output voltage, high	V _{OH}	2.4	V _{DD}	٧	I _{OH} ≈ - 200 μA
Input leakage current, low	I _{LIL}		-10	μΑ	V _{IN} = 0 V
Input leakage current, high	I _{LIH}		+10	μΑ	$V_{IN} = V_{DD}$
Output leakage current, low	l _{LOL}		-10	μА	V _{OUT} = +0.45 V
Output leakage current, high	ILOH		+10	μА	V _{OUT} = V _{DD}
V _{DD} supply current	I _{DD}		10	mA	φ _{CY} = 125 ns
	I _{DD1}		500	μА	$\phi_{\rm CY}=125~{\rm ns}$
			250	μА	φ _{CY} = 250 ns
			100	μА	Clock stopped



AC Characteristics; Main System Side $T_A = -10 \text{ to } +70^{\circ}\text{C}; V_{DD} = +5 \text{ V} \pm 10\%; \text{ MFM data transfer} = 500 \text{ kb/s (8 MHz), 250 kb/s (4 MHz)}$

			8-MI	iz Oper	ation	4-MI	Iz Oper	ation		
Parameter	Figure	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Conditions
Clock cycle	2	Фсч	120	125	500	240	250	500	ns	
Clock width, high/low	2	ϕ_{θ}	40			40			ns	_
Clock rise time	2	ϕ_{R}			20			20	ns	-
Clock fall time	2	ϕ_{F}		-	20			20	ns	-
A0, CS, DACK setup time to RD	3	t _{AR}	0			0			ns	-
A0, CS, DACK hold time from RD	3	t _{RA}	0			0			ns	-
RD pulse width	3	tan	200			200			ns	-
Data access time from RD ↓	3	t _{RD}			140			140	ns	_
Data float delay time from RD ↑	3	tor	10		85	10		85	ns	-
A0, CS, DACK setup time to WR	4	t _{AW}	0			0			ns	-
A0, CS, DACK hold time to WR	4	t _{WA}	0			0			ns	-
WR pulse width	4	tww	200			200			ns	-
Data setup time to WR	4	tow	100			100			ns	-
Data hold time from WR	4	twp	0			0			ns	-
INT delay time from RD↑	3	t _{RI}			400			400	ns	Data transfer in
INT delay time from ₩Ã ↑	4	twi			400		_	400	ns	non-DMA mode
DRQ cycle time	5	tMCY	13			26			μS	9.MU2. d = 105.pa
DACK ↓ response time from DRQ ↑	5	t _{MA}	200			400			ns	8-MHz: $\phi_{CY} = 125 \text{ ns}$ 4-MHz: $\phi_{CY} = 250 \text{ ns}$
RD ↓ response time from DRQ ↑	5	t _{MR}	125			250			ns	•
WR ↓ response time from DRQ ↑	5	t _{MW}	250			500			ns	•
DRQ delay time from DACK ↓	5	t _{AM}			140			140	ns	
DACK pulse width	5	t _{AA}	2			2		170		
WR/RD response time from DRQ ↑	5	t _{MRW}			12			12	Φ CΥ	
TC pulse width	5	t _{TC}	60			60		1£	μs ns	
RESET pulse width	6	t _{RST}	14			14		<u> </u>		
Clock hold time at standby	7	twc	32			32			Фсү	
Clock setup time at standby release	7	tcw	16			16			φcγ	
NT response time from DRQ ↓	8	t _{MI}	60		77	60		77	φ _{CY}	PDTGGGG
NT ↑ to DACK ineffective	8	t _{IA}			1			77	ФСҮ	μPD72065B only
		-1∕^							φ _C Υ	



AC Characteristics; Drive Side

 $T_A = -10$ to $+70^{\circ}$ C; $V_{DD} = +5$ V $\pm 10\%$; MFM data transfer = 500 kb/s (8 MHz), 250 kb/s (4 MHz)

			8-MHz	Орега	stion	4-MHz	Opera	tion		
Parameter	Figure	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Conditions
WCLK cycle time	9	†CY		16			16		Фсч	MFM = 0
				8			8		ΦCY	MFM = 1
WCLK width, high	9	t _g	80	250	350	160	500	700	ns	8-MHz: $\phi_{CY} = 125 \text{ ns}$ 4-MHz: $\phi_{CY} = 250 \text{ ns}$
WCLK, RDATA, WINDOW rise time	9	t _R			20			20	ns	
WCLK, RDATA, WINDOW fall time	9	t _F			20			20	ns	_
PS0, PS1 delay time from WCLK	9	t _{CP}	10		80	10			ns	•
WDATA delay time from WCLK	9	t _{CD}	10		80	10			ns	•
WE delay time from WCLK	9	tcwe	10		80	10			ns	•
WDATA width	9	tWDD	t ₀ - 50			t ₀ - 50			ns	•
RDATA active time high	10	t _{RDD}	40			40			ns	•
WINDOW cycle time	10	twcy		2			4		μs	MFM = 0
				1			2		μs	MFM = 1
WINDOW setup time to RDATA	10	twap.	15			15			ns	
WINDOW hold time from RDATA	10	tRDW	15			15			ns	•
US0, US1 setup time to SEEK	11	tus	12			24			μs	8-MHz: $\phi_{CY} = 125 \text{ ns}$
SEEK setup time to DIR	11	t _{SD}	7			14			μs	- 4-MHz; φ _{CY} = 250 ns _ (Note 1)
DIR setup time to STEP	11	t _{DST}	1			2			μs	. (1010 1)
US0, US1 hold time from STEP	11	tstu	5			10			μs	•
STEP active time high	11	tSTP	6	7	8	12	14	16	μs	-
US0, US1 hold time after SEEK	11	tsu	15			30			μs	-
SEEK hold time from DIR	11	t _{OS}	30			60	-		μs	-
DIR hold time after STEP	11	tsтр	24	=	,	48			дз	-
STEP cycle time	11	tsc	33		***	66			με	-
FLTR active time high	11	t∈n	8		10	16		20	μs	-
INDEX level high	12	фок	4			4			φ _{CY}	-

Notes:

- For the parameters on figures 11 and 12, the minimum values are 50 ns less than the values (μs) specified in the table. For example, 10 μs is actually 9.950 μs.
- (2) While the unit under test is performing a seek operation, the SENSE DEVICE STATUS command is being executed for the other devices.



Figure 1. Voltage Thresholds for Timing Measurements

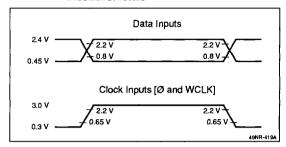


Figure 2. Clock Waveform

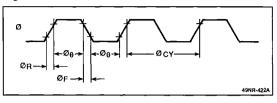


Figure 3. Read Operation

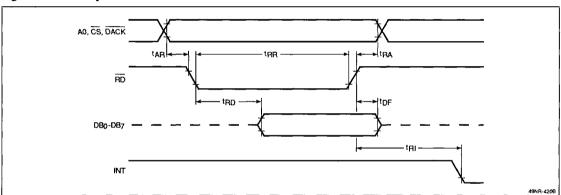


Figure 4. Write Operation

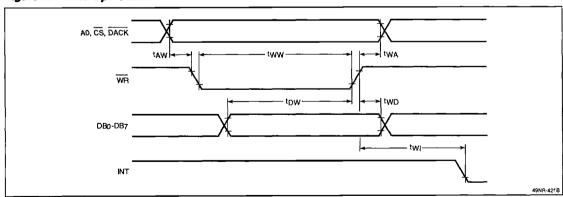




Figure 5. DMA Operation

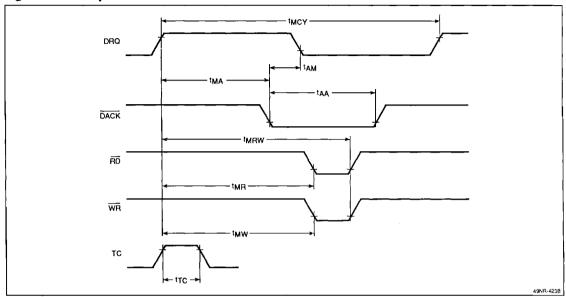


Figure 6. RESET Waveform

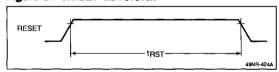


Figure 7. Standby Operation

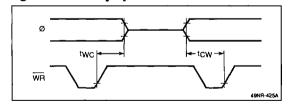


Figure 8. Overrun Operation (µPD720658)

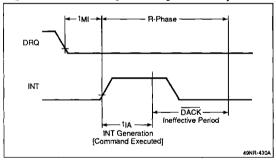




Figure 9. FDD Write Operation

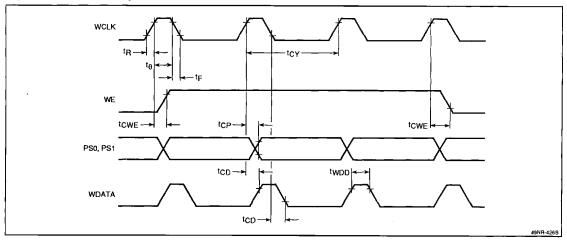


Figure 10. FDD Read Operation

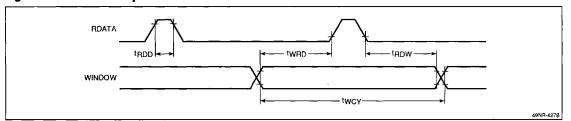


Figure 11. Seek Operation

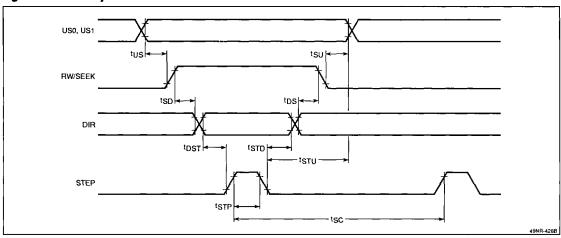
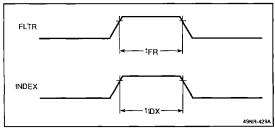




Figure 12. FLTR and INDEX Waveforms



COMPARISON, µPD72065 VS µPD72065B

The μ PD72065B is a functionally enhanced version of the μ PD72065. Differences are explained below.

Overrun Bit (OR)

In the μ PD72065, when executing a read- or write-type command (except READ ID and SCAN types), the result status OR bit is not set if there is an overrun on the final byte of a sector. An improvement in the μ PD72065B allows it to set the OR bit in any situation.

DRQ Reset

When an overrun occurs, the μ PD72065 needs the \overline{DACK} input to reset DRQ. If \overline{DACK} is not available, an external DMA controller continues operating even after the FDC enters the R-phase, and stored result status may be transferred accidentally as ordinary data.

On the other hand, the $\mu\text{PD7}2065B$ resets DRQ automatically just before the R-phase entry and independent of the DACK input. See AC Characteristics for DRQ reset timing.

Clock Synchronization

The μ PD72065 does not require synchronization between the ϕ clock and WCLK inputs.

VERSION Command

The VERSION command distinguishes the µPD72065B from other devices. The ST0 response to the command is:

Part No.	ST0 Value
μPD72065	80H
μPD72065B	90H

COMPARISON, µPD72065/65B VS µPD765A/B

Table 1 shows differences in the parameters and features of the FDCs.

Table 1. μPD72065/65B and μPD765A/B

Parameter	μPD72065/65B	μPD765A/B		
Track format	IBM	77 1.2 ms (4 MHz)		
Tracks to be recalibrated	255			
Skipping time after Index pulse detection	0.2 ms (4 MHz)			
DRQ ↑ to RD ↓ response time				
ϕ_{CY} = 125 ns	1 x φ _{CY}	0.8 μs		
$\phi_{\rm CY}$ = 250 ns	1 x Φ _{CY}	1.6 µs		
FDD response latency after Unit select signal				
$\phi_{\rm CY}$ = 125 ns	2.5 µs	0.5 μs		
$\phi_{\rm CY}$ = 250 ns	5.0 μs	1.0 µs		
Multitrack write by tunnel erase head	Yes	No		
Standby function (Standby command)	Yes	No		
SOFTWARE RESET command	Yes	No		

 $[\]phi_{CY}$ = clock cycle time

DATA FORMAT

Figure 13 shows the data format for FM and MFM modes



Figure 13. Data Format and Timing.

